

**IN THE CLAIMS**

Claims 1-4. (Canceled).

5. (new) A semiconductor epitaxial wafer having an epitaxial layer stacked on a semiconductor substrate, wherein:

plural epitaxial layers are stacked on a front side of the semiconductor substrate; and

an impurity concentration of any one of the plural epitaxial layers is high enough to afford a latch-up resistance and a high-frequency conformity and is higher than impurity concentrations of the semiconductor substrate and other epitaxial layers.

6. (new) A semiconductor epitaxial wafer having an epitaxial layer stacked on a semiconductor substrate, wherein:

plural epitaxial layers are stacked on a front side of the semiconductor substrate;

an impurity concentration of any one of the plural epitaxial layers is high enough for the formation of a gettering site and is higher than impurity concentrations of the semiconductor substrate and other epitaxial layers; and

an impurity concentration of the semiconductor substrate is at a level of suppressing impurity discharge from the semiconductor substrate.

7. (new) The semiconductor epitaxial wafer according to claim 5, wherein an impurity concentration of the epitaxial layer being in contact with the semiconductor substrate among the plural epitaxial layers is higher than the impurity concentrations of the semiconductor substrate and the other epitaxial layers.

8. (new) A semiconductor epitaxial wafer having an epitaxial layer stacked on a semiconductor substrate, wherein:

plural epitaxial layers are stacked on a front side of the semiconductor substrate;

an impurity concentration of a high-concentration epitaxial layer among the plural epitaxial layers is  $2.77 \times 10^{17}$  to  $5.49 \times 10^{19}$  (atoms/cm<sup>3</sup>); and

an impurity concentration of the semiconductor substrate is  $1.22 \times 10^{14}$  to  $1.46 \times 10^{16}$  (atoms/cm<sup>3</sup>).

9. (new) A semiconductor epitaxial wafer having an epitaxial layer stacked on a semiconductor substrate, wherein:

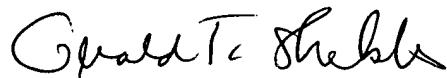
plural epitaxial layers are stacked on a front side of the semiconductor substrate;

a resistivity of a high-concentration epitaxial layer among the plural epitaxial layers is 0.002 to 0.1 ( $\Omega$  cm); and

a resistivity of the semiconductor substrate is 1 to 100 ( $\Omega$  cm).

10. (new) The semiconductor epitaxial wafer according to claim 5, wherein a high-concentration epitaxial layer among the plural epitaxial layers contains boron.

Respectfully submitted,  
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